

## IN THE CLAIMS

Please cancel claims 77-90. Please amend the claims as follows.

For the Examiner's convenience, all pending claims are included below.

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1-62 (Cancelled /

63. (Previously amended) A microelectronic structure comprising:

a substrate;

61 a gate electrode formed over the substrate and defining an underlying channel region in the substrate, said gate electrode having a barrier layer formed on a sidewall of the gate electrode to prohibit the silicidation of the sidewall;

a source/drain extension formed in the substrate adjacent the gate electrode and encroaching laterally into the underlying channel region a first distance, the source/drain extension having a first silicide layer formed therein, the first silicide encroaching laterally into the underlying channel region a second distance less than the first distance; and

a source/drain region formed in the substrate adjacent the source/drain extension and having an activated doped region with a second silicide layer disposed therein, the activated doped region and the second silicide layer are aligned with a spacer disposed along sidewalls of the gate electrode such that the activated doped region and the second silicide layer encroach laterally into the underlying channel region a third distance less than the second distance, [said second silicide layer formed after removing a portion of said barrier layer formed over a top surface of the gate electrode,] said source/drain extension having less dopant concentration than the activated doped region[, and the source/drain extension and the first silicide layer are aligned

with the gate electrode to have the less dopant concentration of the extension reside between the channel region and the activated doped region].

64. (Previously amended) The microelectronic structure of claim 63, wherein the activated doped region is thicker than the source/drain extension.

65. (Previously amended) The microelectronic structure of claim 63, wherein the second silicide layer is thicker than the first silicide layer.

66. (Previously amended) The microelectronic structure of claim 63, wherein the activated doped region and the source/drain extension comprise ion implanted material.

67. (Previously added) The microelectronic structure of claim 63, wherein the first and second silicide layers comprises different metals.

68. (Previously added) The microelectronic structure of claim 63, wherein the first and second silicide layers comprise a same metal.

69. (Previously added) The microelectronic structure of claim 63, wherein the second silicide layer comprises  $\text{CoSi}_2$ .

70. (Previously added) The microelectronic structure of claim 63, wherein the second silicide layer comprises  $\text{TiSi}_2$ .

71. (Previously amended) The microelectronic structure of claim 63, wherein the second silicide layer comprises nickel silicide.

61 72. (Original) The microelectronic structure of claim 63, wherein the first silicide layer comprises  $\text{CoSi}_2$ .

73. (Original) The microelectronic structure of claim 63, wherein the first silicide layer comprises  $\text{TiSi}_2$ .

74. (Previously amended) The microelectronic structure of claim 63, wherein the gate electrode [having] has a third silicide layer formed on the top surface of the gate electrode.

75. (Previously amended) The microelectronic structure of claim 63, wherein the barrier layer comprises silicon nitride.

76. (Previously amended) The microelectronic structure of claim 63, wherein the source/drain extension is [approximately 300-500] more than 400 angstroms in thickness.

77-90 (Cancelled) ✓

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